

General Description

The WSF4095 is the highest performance trench N-Channel MOSFET with extreme high cell density, which provide excellent RDSON and gate chargefor most of the synchronous buck converterapplications.

The WSF4095 meet the RoHS and GreenProduct requirement 100% EAS guaranteed withfull function reliability approved.

Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- 100% EAS Guaranteed
- Green Device Available

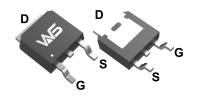
Product Summery

BV _{DSS}	R _{DSON}	I _D
40V	4mΩ	95A

Applications

- SMPS Synchronous Rectification.
- Load Switch.
- DC-DC Conversion.

TO-252 Pin Configuration





$5 \, \text{Vgc`i hY`AU]} \text{a i a `FUh]b[} \text{g\'a\',} \text{a\'} \text{m\'e} \text{ `°O\'AV} \text{ | $^{\bullet\bullet}$ AU @$|, $ \tilde{a}^{\wedge}$ he[$ e^{\circ}$ aD $] }$

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	40	V
V_{GS}	Gate-Source Voltage	±20	V
I _D @T _C =25℃	Continuous Drain Current, V _{GS} @ 10V ¹	95	Α
I _D @T _C =100℃	Continuous Drain Current, V _{GS} @ 10V ¹	50	Α
I _D @T _A =25℃	Continuous Drain Current, V _{GS} @ 10V ¹	18	Α
I _D @T _A =70℃	Continuous Drain Current, V _{GS} @ 10V ¹	14	Α
I _{DM}	Pulsed Drain Current ² ·T _C =25°C	224	Α
EAS	Avalanche Energy, Single pulse,L=0.1mH	51	mJ
I _{AS}	Avalanche Current, Single pulse,L=0.1mH	32	Α
P _D @T _C =25℃	Total Power Dissipation ⁴	54	W
P _D @T _C =100 ℃	Total Power Dissipation ⁴	22	W
T _{STG}	Storage Temperature Range -55 to 150		℃
T_J	Operating Junction Temperature Range -55 to 150		°C

Thermal Data

Symbol	Parameter	Тур.	Max.	Unit
$R_{ heta JA}$	Thermal Resistance Junction-Ambient ¹		50	°C/W
$R_{ heta JC}$	Thermal Resistance Junction-Case ¹		2.3	°C/W



Electrical Characteristics (T_J=25°C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit	
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V , I _D =250uA	40			V	
D	Static Drain-Source On-Resistance ²	V _{GS} =10V, I _{DS} =20A		4	4.8	mΩ	
R _{DS(ON)}		V _{GS} =4.5V, I _{DS} =15A		5.2	6.8	mΩ	
V _{GS(th)}	Gate Threshold Voltage	V_{GS} = V_{DS} , I_D =250uA	1.3	1.7	2.5	V	
	Danie Course Lookene Course	V_{DS} =32V , V_{GS} =0V , T_J =25 $^{\circ}\mathrm{C}$			1		
I _{DSS}	Drain-Source Leakage Current	V_{DS} =32V , V_{GS} =0V , T_J =85 $^{\circ}\mathrm{C}$			30	uA	
I _{GSS}	Gate-Source Leakage Current	V_{GS} = $\pm 20V$, V_{DS} = $0V$			±100	nA	
gfs	orward Transconductance	V_{DS} =5V , I_D =20A		31		S	
R_g	Gate Resistance	V_{DS} =0V , V_{GS} =0V , f=1MHz		1	2	Ω	
Qg	Total Gate Charge (10V)			11.5			
Q_gs	Gate-Source Charge	V_{DS} =20V , V_{GS} =10V , I_D =20A		5.2		nC	
Q_gd	Gate-Drain Charge			2.6			
T _{d(on)}	Turn-On Delay Time			7.7	14		
Tr	Rise Time	V_{DD} =20V, R_L =20 Ω , I_{DS} =1A,		14.3	26	no	
$T_{d(off)}$	Turn-Off Delay Time	V_{GEN} =10V, R_{G} =6 Ω		26.6	48	ns	
T _f	Fall Time			32.6	59		
C _{iss}	Input Capacitance			1645	2139		
Coss	Output Capacitance	V _{DS} =20V , V _{GS} =0V , f=1MHz		385	pF		
C _{rss}	Reverse Transfer Capacitance			55			

Diode Characteristics

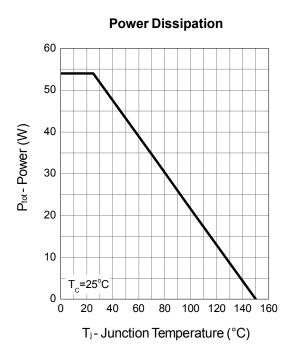
Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
Is	Continuous Source Current ^{1,6}	V _G =V _D =0V , Force Current			25	Α
V_{SD}	Diode Forward Voltage ²	V _{GS} =0V , I _S =20A , T _J =25℃		0.75	1.1	V
t _{rr}	Reverse Recovery Time	1- 004 JUL 4004 - T 05°C		28		nS
Q _{rr}	Reverse Recovery Charge	lF=20A,dl/dt=100A/μs,T _J =25℃		20		nC

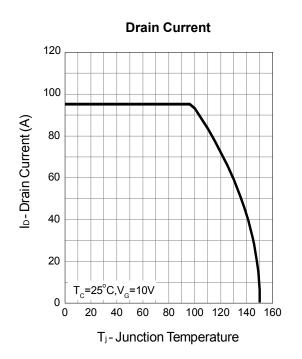
Note:

- 1. The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper,t<10sec.
- 2. The data tested by pulsed , pulse width $\leqq 300 \text{us}$, duty cycle $\leqq 2\%$
- $\overline{3}$.The EAS data shows Max. rating . The test condition is V_Ds=20V,V_Gs=10V,L=0.1mH,I_As=32A
- 4. The power dissipation is limited by 150 $^{\circ}$ C junction temperature 5. The Min. value is 100% EAS tested guarantee.
- 6. The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

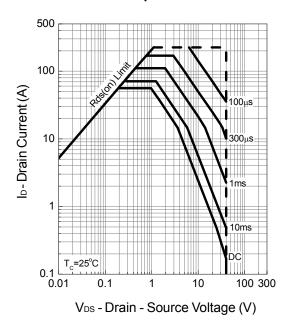


Typical Characteristics

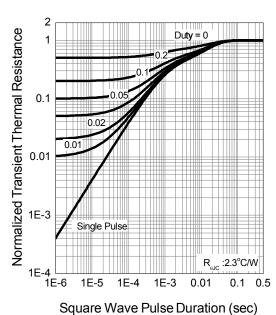




Safe Operation Area



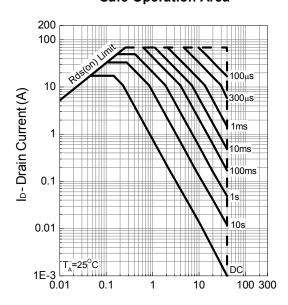
Thermal Transient Impedance





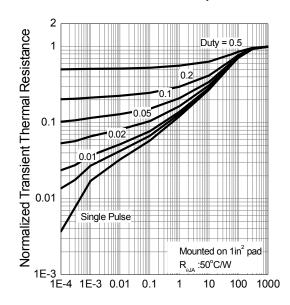
Typical Characteristics (Cont.)

Safe Operation Area



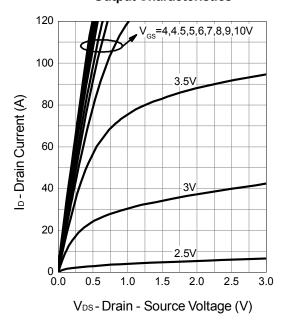
V_{DS} - Drain - Source Voltage (V)

Thermal Transient Impedance

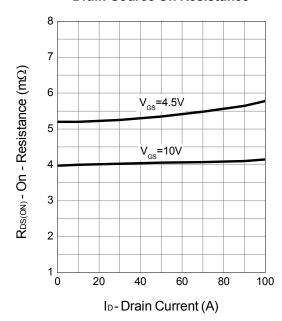


Square Wave Pulse Duration (sec)

Output Characteristics



Drain-Source On Resistance





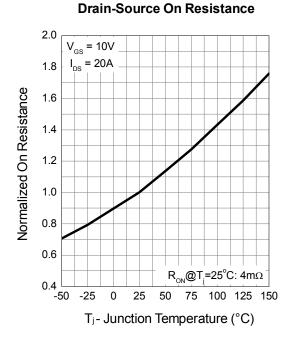
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Typical Characteristics (Cont.)

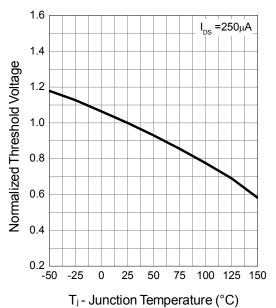
V_{GS} - Gate - Source Voltage (V)

9 10

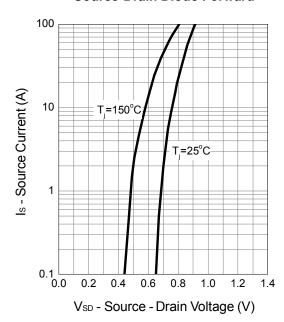
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Gate Threshold Voltage

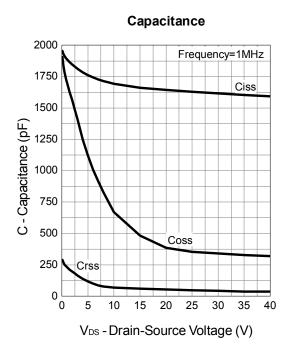


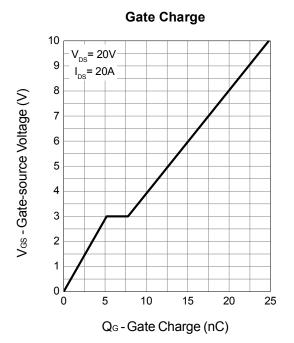
Source-Drain Diode Forward

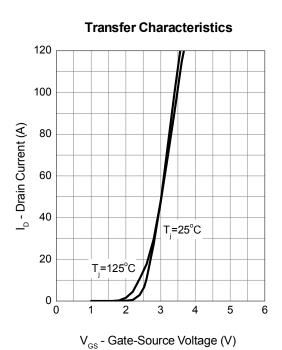




Typical Characteristics (Cont.)

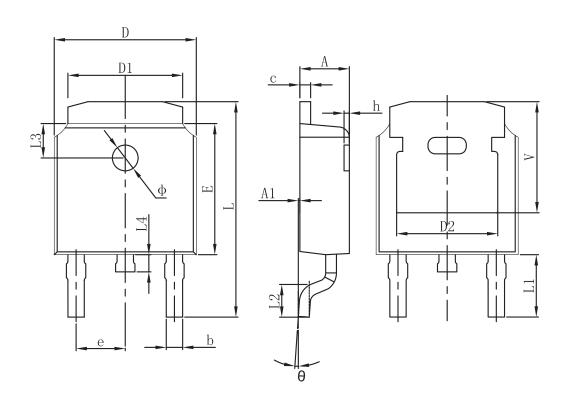








Packaging information



Symbol	Dimensions In Millimeters		Dimensions In Inches		
Syllibol	Min.	Max.	Min.	Max.	
Α	2.200	2.400	0.087	0.094	
A1	0.000	0.127	0.000	0.005	
b	0.635	0.770	0.025	0.030	
С	0.460	0.580	0.018	0.023	
D	6.500	6.700	0.256	0.264	
D1	5.100	5.460	0.201	0.215	
D2	4.830	REF.	0.190	REF.	
E	6.000	6.200	0.236	0.244	
е	2.186	2.386	0.086	0.094	
L	9.712	10.312	0.382	0.406	
L1	2.900 REF.		0.114 REF.		
L2	1.400	1.700	0.055	0.067	
L3	1.600 REF.		0.063 REF.		
L4	0.600	1.000	0.024	0.039	
Ф	1.100	1.300	0.043	0.051	
θ	0°	8°	0°	8°	
h	0.000	0.300	0.000	0.012	
V	5.250	REF.	0.207 REF.		



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